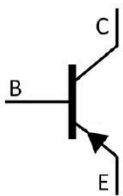


Rev.F Apr.-2017

SOT-23 PNP Silicon PNP transistor in a SOT-23 Plastic Package.

Low frequency.

Low frequency power amplifier.

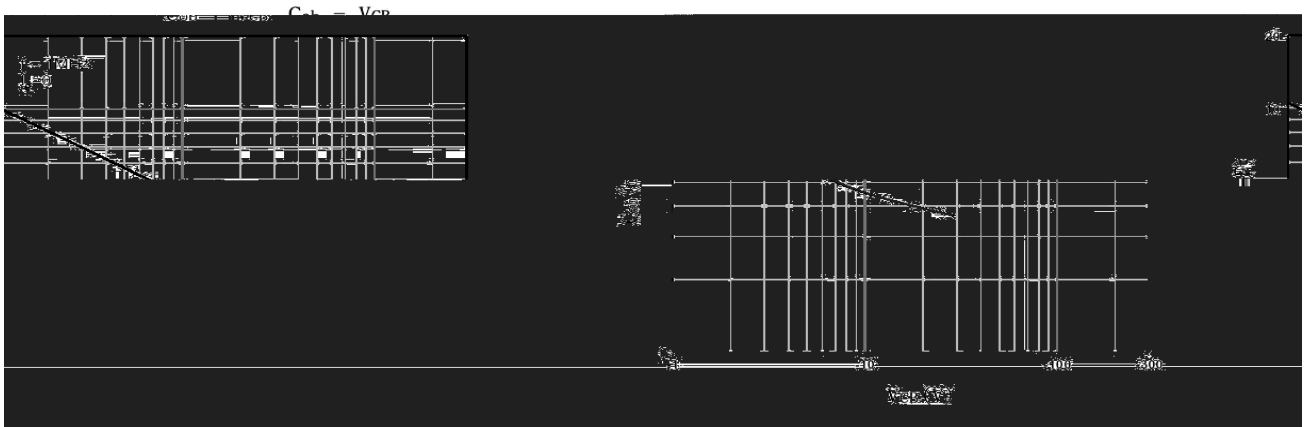
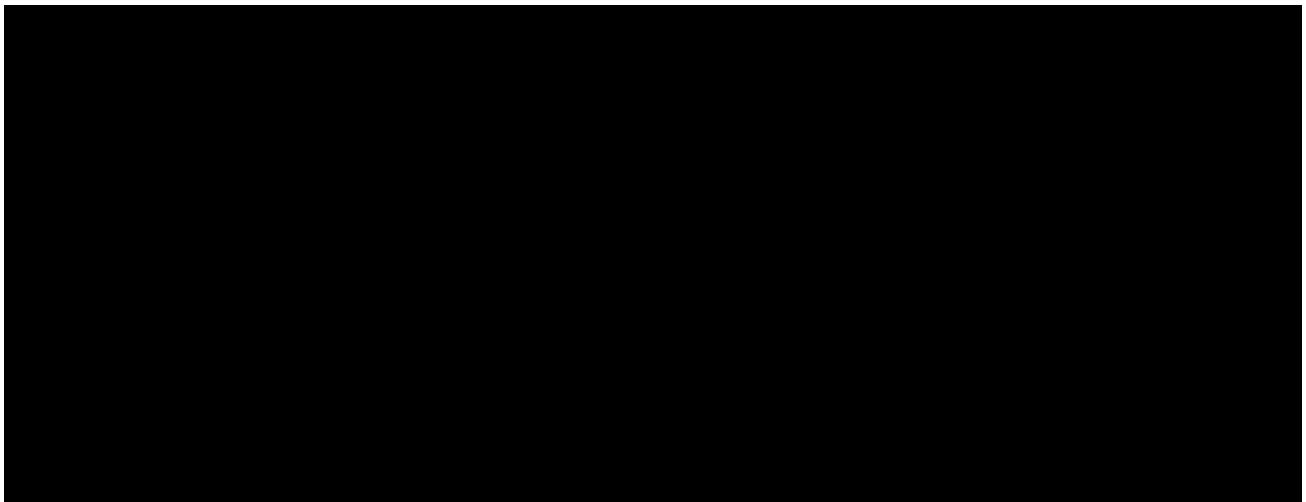
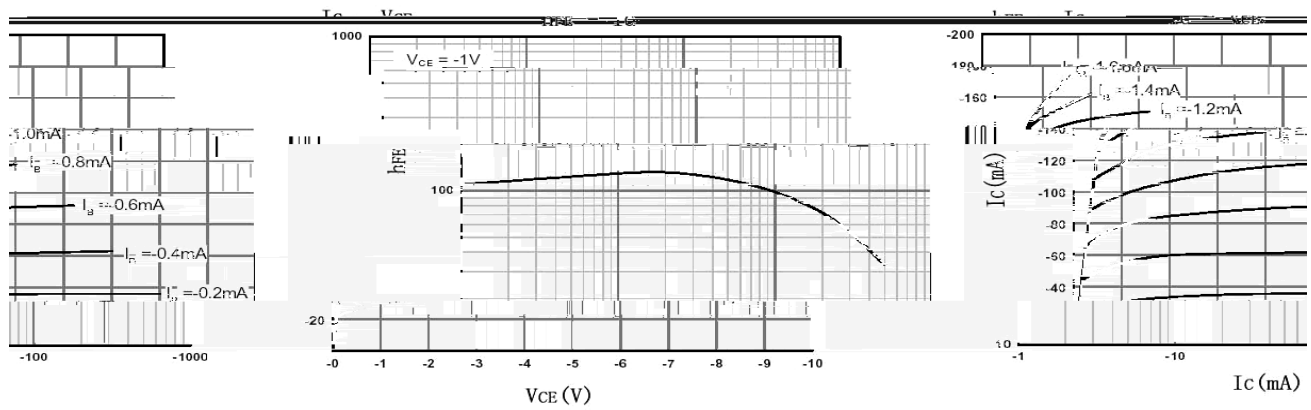


PIN 1 Base PIN 2 Emitter PIN 3 Collector

h_{FE} Classifications Symbol	O	Y
h_{FE} Range	70~140	120~240
Marking	HF1O	HF1Y

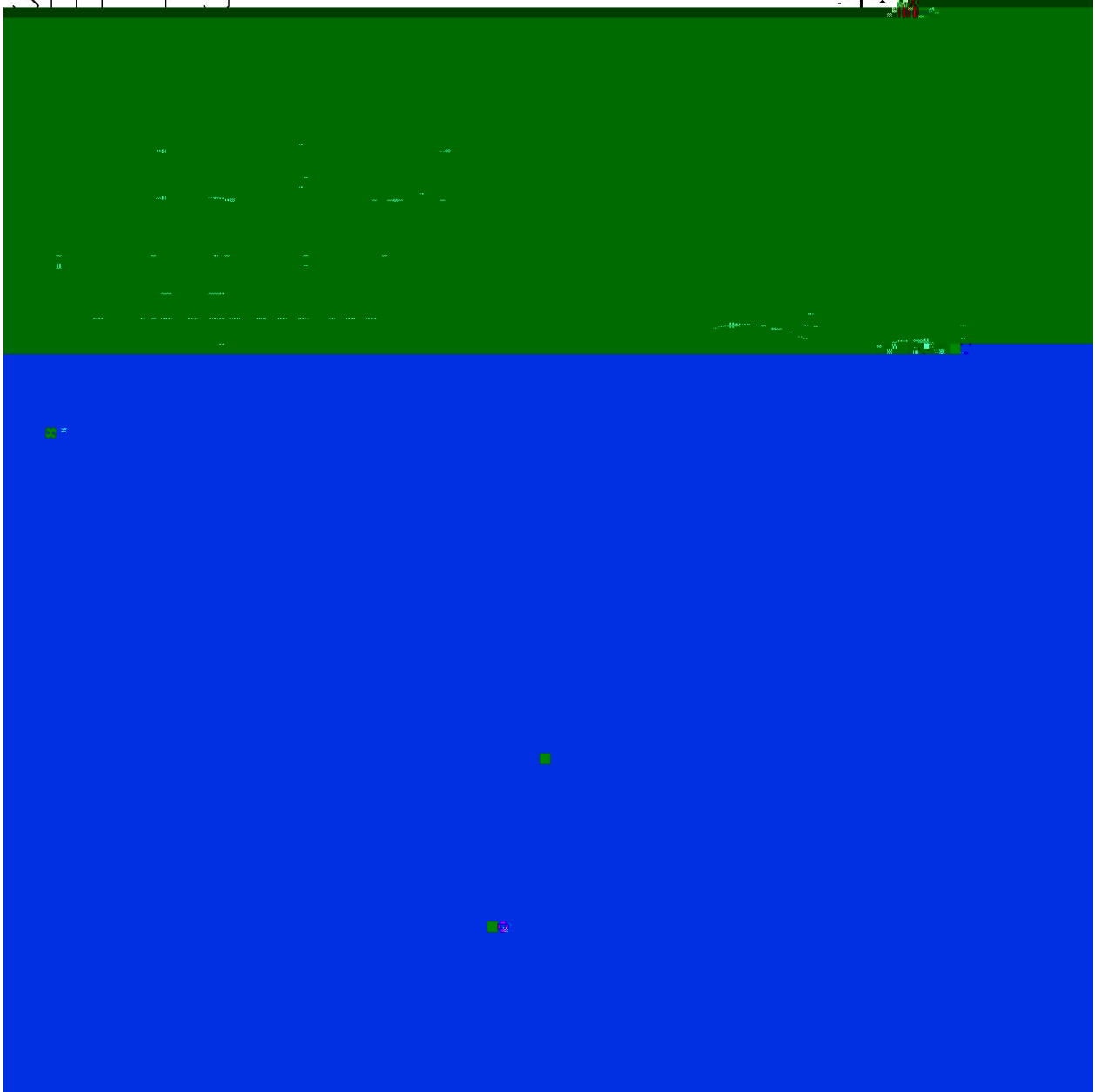
Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-35	V
Collector to Emitter Voltage	V_{CEO}	-30	V
Emitter to Base Voltage	V_{EBO}	-5.0	V
Collector Current	I_C	-500	mA
Collector Power Dissipation	P_C	150	mW
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55~150	

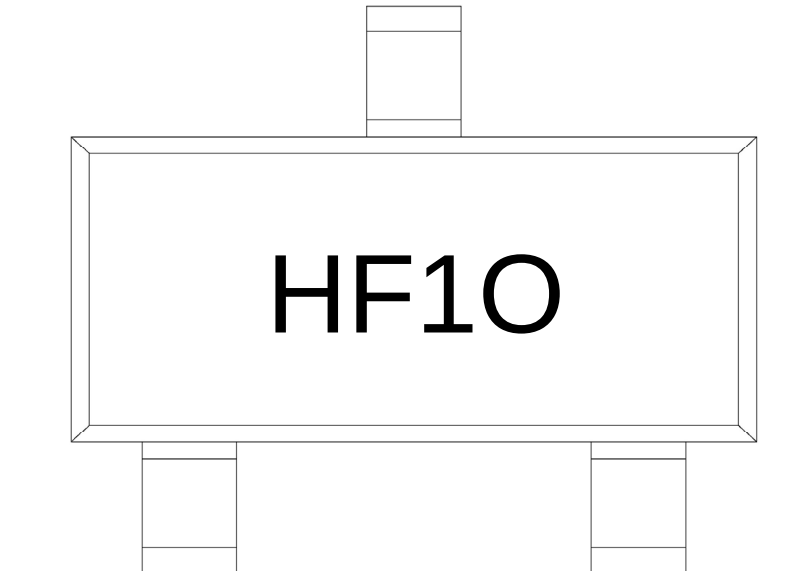
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector Cut-Off Current	I_{CBO}	$V_{CB}=-35V$ $I_E=0$			-0.1	A
Emitter Cut-Off Current	I_{EBO}	$V_{EB}=-5.0V$ $I_C=0$			-0.1	A
DC Current Gain	$h_{FE(1)}$	$V_{CE}=-1.0V$ $I_C=-100mA$	70		240	
	$h_{FE(2)}$	$V_{CE}=-6.0V$ $I_C=-400mA$	25			
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=-100mA$ $I_B=-10mA$		-0.1	-0.25	V
Base to Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C=-100mA$ $V_{CE}=-1.0V$		-0.8	-1.0	V
Transition Frequency	f_T	$I_C=-20mA$ $V_{CE}=-6.0V$		200		MHz
Collector Output Capacitance	C_{ob}	$V_{CB}=-6.0V$ $I_E=0$ $f=1.0MHz$		13		pF



SNT-23

单位:





H

F1

O h_{FE}

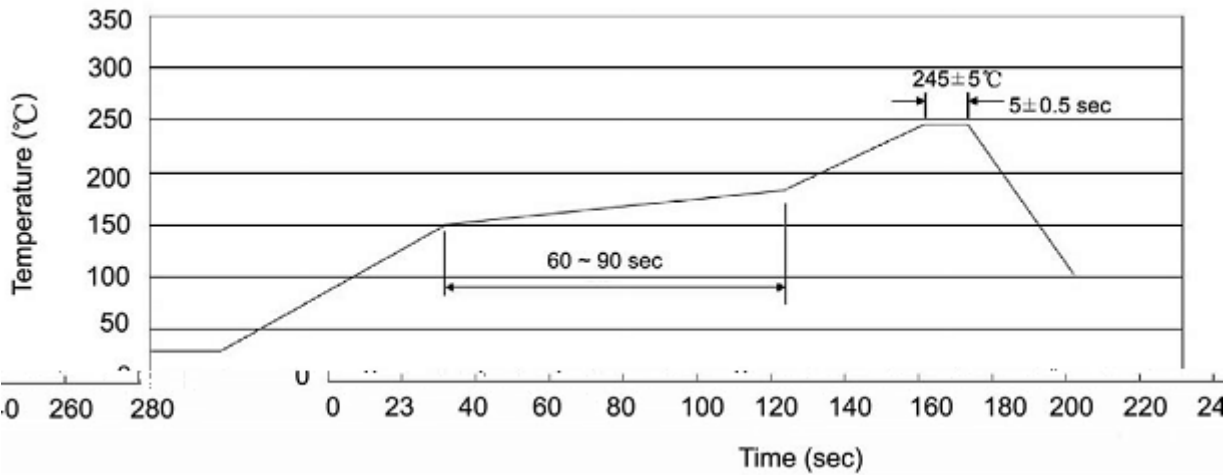
Note:

H Company Code

F1 Product Type Code

O h_{FE} Classifications Symbol Code

Temperature Profile for IR Reflow Soldering(Pb-Free)



Note:

- 1

25 150

60 90sec;

1.Preheating:25~150 , Time:60~90sec.
- 2

245±5

5±0.5sec;

2.Peak Temp.:245±5 , Duration:5±0.5sec.
- 3

2 10 /sec.

3. Cooling Speed: 2~10 /sec.

260±5 10±1 sec. Temp.:260±5 Time:10±1 sec

/ REEL

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm ³)		
	Units/Reel 只/卷盘	Reels/Inner Box 卷盘/盒	Units/Inner Box 只/盒	Inner Boxes/Outer Box 盒/箱	Units/Outer Box 只/箱	Reel	Inner Box 盒	Outer Box 箱
SOT-23	3,000	10	30,000	6	180,000	7" x8	180×120×180	390×385×205